Studies of indium influence on transport properties of partially filed In_xCo₄Sb₁₂

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Studies of partially filled n-type In_xCo₄Sb₁₂ skutterudite compounds has been recently reported showing interesting thermoelectric properties at moderate temperatures.

In this paper, we have focused our investigations on more detailed recognition of transport properties in $In_xCo_4Sb_{12}$. Polycrystalline samples of indium partially filled CoSb₃ have been prepared by a typical solid-state reaction. In order to recognize indium behaviour in skutterudite structural voids, neutron powder diffraction studies on a temperature range 4 – 300K have been carried out on selected samples preceded by a X-ray powder diffraction structural studies. Measurements of the electrical resistivity, thermoelectric power and thermal conductivity have been performed between 4 and 800 K. Hall carrier concentrations and mobilities have been determined from 4 to 350 K. The influence of the indium partial filling on the transport properties of $In_xCo_4Sb_{12}$ and correlation between determined structural parameters and thermal conductivity are presented and discussed.

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